



Bridging the Price/Performance Gap Between Silicon Drift and Silicon PIN Diode Detectors



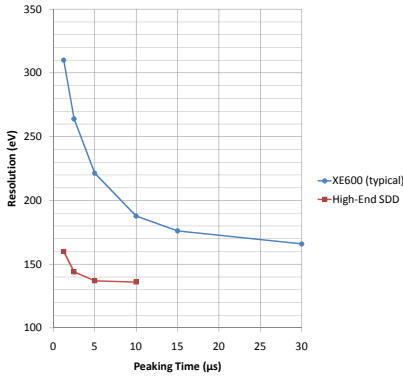
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at booth #204

High End SDD vs. Moxtek XE600 PIN Diode Detector



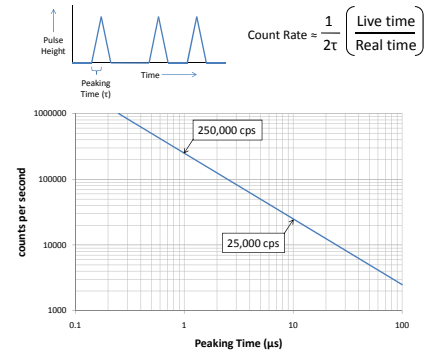
The XE600 detector uses a 400 μm PIN diode. The resolution is measured at 5.9 keV. All measurements are made at -25°C.

The SDD has much **better resolution** performance, but it also has about **3 times the cost** of a PIN diode detector.

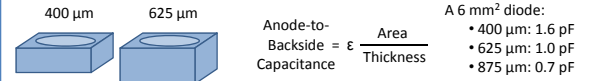
Count Rate versus Peaking Time

When the signal from an x-ray photon passes through a shaping amplifier, it is converted into a voltage pulse with a given shape (commonly a triangular shape). A stream of detected photons results in a series of peaks—each peak representing a detected photon (or “count”). The peaking time (t) is the time between the beginning of the voltage pulse and its peak.

Shorter peaking times make it possible to collect **more counts in a given amount of time**.



Reducing Diode Capacitance

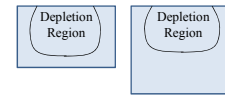


Thicker Diode → Less Capacitance

→ Better Resolution

Depletion Region:

Thicker Depletion Region → Less Capacitance



$$\text{Depletion Thickness} = \sqrt{\frac{2 \epsilon V_{\text{bias}}}{q N_d}}$$

A Thicker Depletion Region Requires Either:

1. Larger V_{bias}
2. Smaller N_d (Higher Resistivity)

Additional Challenge:

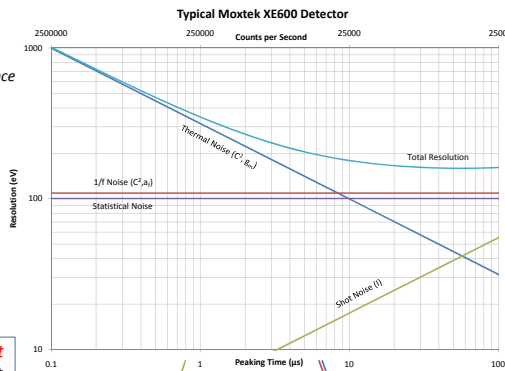
Leakage Current \propto Depleted Volume

Solutions:

1. Very Low Leakage Current Process
2. Lower operating temperature

Resolution Components

C: Total Capacitance
 g_m : JFET Transconductance
 α_f : 1/f Noise Coefficient
 I: Leakage Current

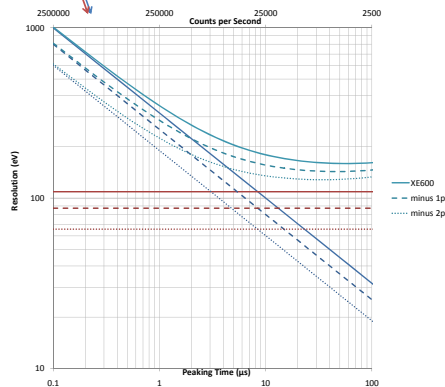
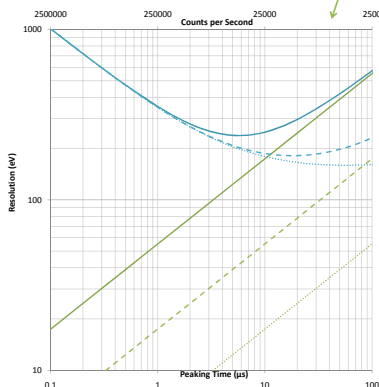


Lower leakage current
 → **Better Resolution** at **Longer Peaking Times**

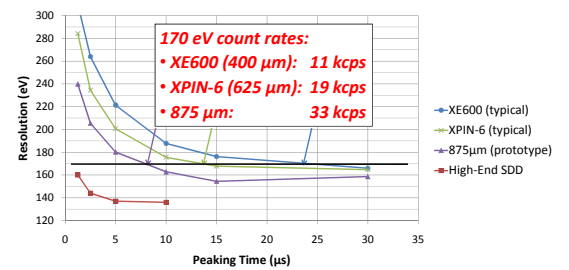
Leakage Current

Capacitance

Lower Capacitance
 → **Better Resolution** at **Shorter Peaking Times**



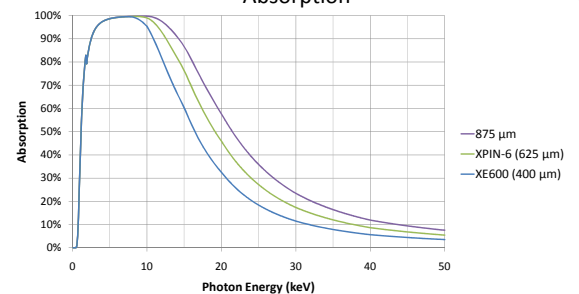
Resolution Measurements



XPIN-6 measurements are made at -25°C and with a diode bias of 130 V. Measurements with the prototype 875 μm detector were made at -45°C and with a diode bias of 300 V.

Achieving 875-μm performance comparable to what is shown here with lower biases and higher operating temperatures are challenges to be resolved.

Absorption



Above about 25 keV, absorption is proportional to thickness for these thicknesses, so an **875 μm diode** has more than **twice the absorption** as the 400-μm-thick XE600.